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October 2013

# ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3

EcoSPARK<sup>®</sup> 300mJ, 400V, N-Channel Ignition IGBT

#### **General Description**

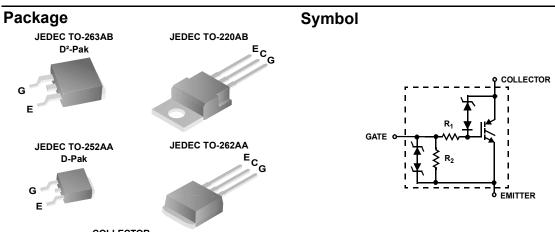
The ISL9V3040D3S, ISL9V3040S3S, ISL9V3040P3, and ISL9V3040S3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D<sup>2</sup>-Pak (TO-263), and TO-262 and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

**EcoSPARK®** devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

Formerly Developmental Type 49362

#### **Applications**

- Automotive Ignition Coil Driver CircuitsCoil- On Plug Applications
- Features
- Space saving D-Pak package availability
- SCIS Energy = 300mJ at T<sub>1</sub> =  $25^{\circ}$ C
- Logic Level Gate Drive



COLLECTOR (FLANGE)

## Device Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units V
BV <sub>CER</sub>	Collector to Emitter Breakdown Voltage (I <sub>C</sub> = 1 mA)	430	
BV <sub>ECS</sub>	Emitter to Collector Voltage - Reverse Battery Condition (I <sub>C</sub> = 10 mA)	24	V
E <sub>SCIS25</sub>	At Starting $T_J$ = 25°C, $I_{SCIS}$ = 14.2A, L = 3.0 mHy	300	mJ
E <sub>SCIS150</sub>	At Starting T <sub>J</sub> = 150°C, I <sub>SCIS</sub> = 10.6A, L = 3.0 mHy	170	mJ
I <sub>C25</sub>	Collector Current Continuous, At T <sub>C</sub> = 25°C, See Fig 9	21	A
I <sub>C110</sub>	Collector Current Continuous, At T <sub>C</sub> = 110°C, See Fig 9	17	Α
V <sub>GEM</sub>	Gate to Emitter Voltage Continuous	±10	V
PD	Power Dissipation Total T <sub>C</sub> = 25°C	150	W
	Power Dissipation Derating T <sub>C</sub> > 25°C	1.0	W/°C
Τ <sub>J</sub>	Operating Junction Temperature Range	-40 to 175	°C
T <sub>STG</sub>	Storage Junction Temperature Range	-40 to 175	°C
T <sub>L</sub> Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)		300	°C
T <sub>pkg</sub>	Max Lead Temp for Soldering (Package Body for 10s)	260	°C
ESD	Electrostatic Discharge Voltage at 100pF, 1500 $\Omega$	4	kV

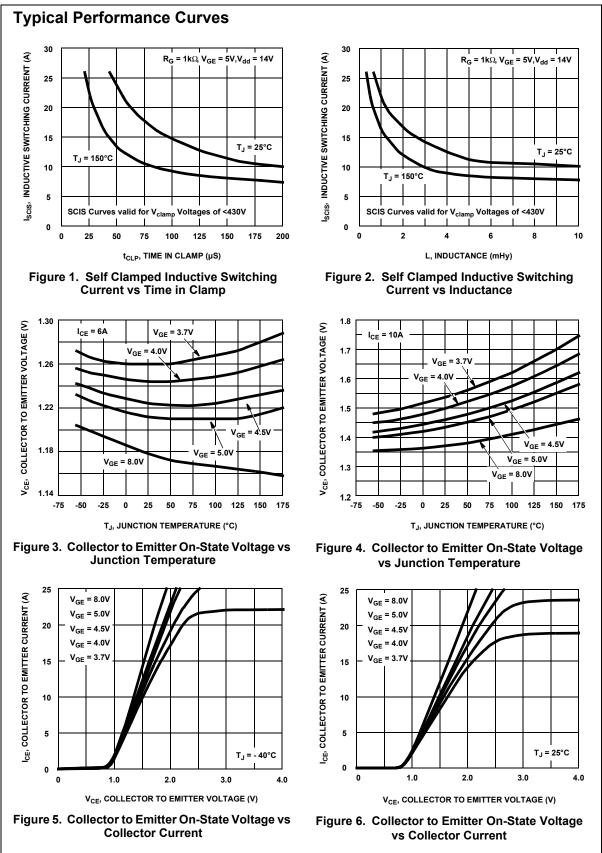
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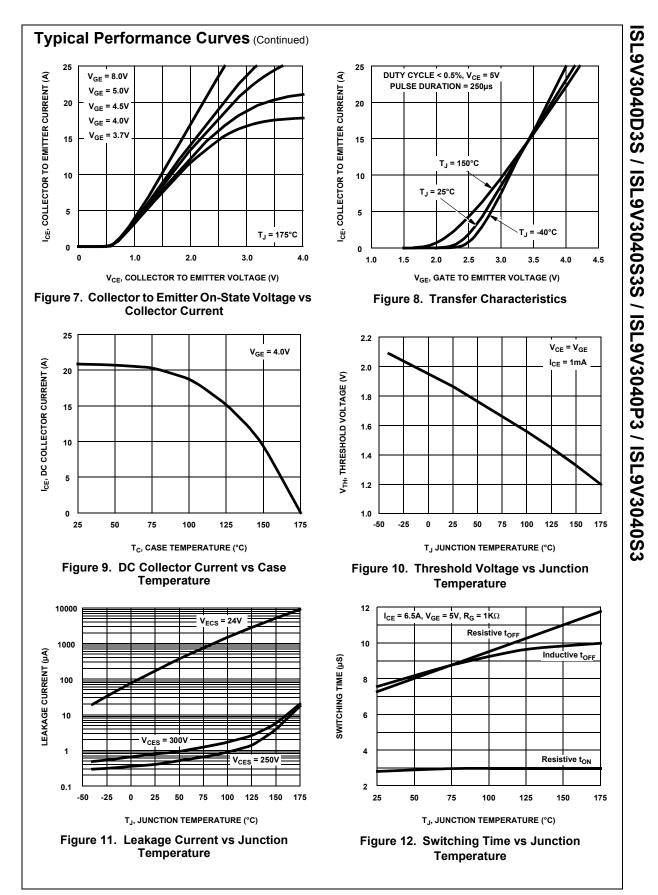
SEMICONDUCTOR®

<b>T</b> State Characteristics $BV_{CER}$ Collector to Emitter Breakdown Voltage $ _{C} = 2mA, V_{GE} = 0, R_G = 1K\Omega, See Fig. 15 T_J = 40 to 150°C370400430VBV_{CES}Collector to Emitter Breakdown Voltage _{C} = 10mA, V_{GE} = 0, R_G = 0, See Fig. 15 T_J = 40 to 150°C390420450VBV_{ECS}Emitter to Collector Breakdown Voltage _{C} = 75mA, V_{GE} = 0, R_G = 182, V_T_J = 40 to 150°C300VBV_{ECS}Gate to Emitter Breakdown Voltage _{C} = 75mA, V_{GE} = 0V, T_C = 25°C300VI_{CER}Collector to Emitter Breakdown Voltage _{GES} = \pm 2mA\pm 12\pm 14-VBV_{ECS}Gate to Emitter Breakdown Voltage _{GES} = \pm 2mA\pm 12\pm 14-VI_{CER}Collector to Emitter Leakage CurrentV_{CER} = 250V, R_G = 150°C1mAI_{ECS}Emitter to Collector Leakage CurrentV_{EC} = 24V, SeeT_C = 25°C1mAR_2Gate to Emitter Resistance70-\Omega\OmegaN_{CE(SAT)}Collector to Emitter Saturation Voltage _C = 10A, V_{CE} = 4.5V, See Fig. 31.581.80VV_{CE(SAT)}Collector to Emitter Saturation Voltage _C = 10A, V_{CE} = 12V, C_{C} - 1.581.80VV_{CE(SAT)}Collector to Emitter Saturation Voltage _C = 10A, V_{CE} = 12V, C_{C} - 1.581.80VV_{CE(SAT)}Collector to Emitter Satur$	Device M	Device Marking Device		P	Package Reel Size		Tape Width		Quantity		
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V3040SISL9V3040S3STO-263ABTubeN/A50Gettrical Characteristics $T_A = 25^{\circ}C$ unless otherwise notedSymbolParameterTest ConditionsMinTypMaxUnitf State Characteristics $BV_{CER}$ Collector to Emitter Breakdown Voltage $I_C = 2mA, V_{OE} = 0, R_G = 180, See Fig. 15 T_3 = 40 to 150^{\circ}C370400430VBV_{CES}Collector to Emitter Breakdown VoltageI_C = 75mA, V_{OE} = 0, See Fig. 15 T_3 = 40 to 150^{\circ}C300420450VBV_{CES}Collector to Emitter Breakdown VoltageI_C = 75mA, V_{OE} = 0V, T_C = 25^{\circ}C30VBV_{CES}Emitter to Collector Breakdown VoltageI_{CES} = 2mA\pm 12\pm 14-VI_{CER}Collector to Emitter Breakdown VoltageI_{CER} = 250V, T_C = 25^{\circ}C-1mABV_{EGS}Gate to Emitter Leakage CurrentV_{CE} = 24V, See Fig. 13T_C = 150^{\circ}C-1mAI_{CER}Series Gate Resistance-70-0000R_2Gate to Emitter Resistance-10K-26K0R_2Gate to Emitter Saturation VoltageI_C = 6A, V_{CE} = 12V, V_{CE} = 1.150^{\circ}C, -1.581.60VV_{CE(SAT)}Collector to Emitter Saturation VoltageI_C = 6A, V_{CE} = 12V, V_{CE} = 1.150^{\circ}C, -1.581.60VV_{CE(SAT)}Collector to Emitter Saturation VoltageI_C = 10A, V_{CE} = 12V, V_{CE} = 1.50$											
ectrical Characteristics $T_A = 25^{\circ}C$ unless otherwise notedSymbolParameterTest ConditionsMinTypMaxUnitf State Characteristics $BV_{CER}$ Collector to Emitter Breakdown Voltage $ _C = 2mA, V_{OE} = 0, R_G = 1K\Omega, See Fig. 15$ $T_J = -40 to 150^{\circ}C$ 370400430V $BV_{CES}$ Collector to Emitter Breakdown Voltage $ _C = 10mA, V_{OE} = 0, R_G = 0, See Fig. 15$ $T_J = -40 to 150^{\circ}C$ 390420450V $BV_{ECS}$ Emitter to Collector Breakdown Voltage $ _C = 75mA, V_{OE} = 0V, G = 0V, R_G = 0, See Fig. 15$ $T_J = -40 to 150^{\circ}C$ 30V $BV_{ECS}$ Emitter to Collector Breakdown Voltage $ _{CES} = 2mA + 12 \pm 14$ -VV $ _{CER}$ Collector to Emitter Breakdown Voltage $ _{CES} = 12mA + 12 \pm 14$ -V $ _{CER}$ Collector to Emitter Leakage Current $V_{CE} = 24V, See Fig. 1$ $T_C = 25^{\circ}C 1 + 12$ mA $I_{ECS}$ Emitter to Collector Leakage Current $V_{CE} = 24V, See Fig. 3$ $T_C = 25^{\circ}C 1 + 14$ mA $R_1$ Series Gate Resistance10K-26K $\Omega$ $R_2$ Gate to Emitter Resistance10K-26K $\Omega$ $V_{CE(SAT)}$ Collector to Emitter Saturation Voltage $V_C = 6A, V_C = 150^{\circ}C, - 1.58$ 1.80V $V_{CE(SAT)}$ Collector to Emitter Saturation Voltage $V_C = 10A, V_C = 12V, See Fig. 1$ -1.7-nC $V_{CE(SAT)}$ Collector to Emitter Saturation Voltage $V_C $							_				
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<b>T</b> State CharacteristicsImage: Constraint of the second sec				o C un	r		Min	Тур	Max	Units	
		Charact						.,,			
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $					$R_G = 1K\Omega$ , See Fig. 15		370	400	430	V	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	BV <sub>CES</sub>	Collector	r to Emitter Breakdown Voltage		$I_{C} = 10$ mA, $V_{GE} = 0$ , R <sub>G</sub> = 0, See Fig. 15		390	420	450	V	
$\begin{array}{c ccr} I_{CER} & Collector to Emitter Leakage Current} & V_{CER} = 250V, \\ R_G = 1K\Omega, \\ See Fig. 11 & T_C = 25^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 1 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 40 & mA \\ \hline T_C = 150^\circ C & - & - & 10 & M \\ \hline T_C = 150^\circ C & - & - & 10 & M \\ \hline T_C = 101 & T_C = 150^\circ C & - & 1.25 & 1.60 & V \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 6A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 10A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 15A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 15A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 15A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 10A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 10A, \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 10A, \\ \hline V_{CE} = 4.5V & See Fig. 14 & - & 1.70 & - & nC \\ \hline V_{GE} = 5V, See Fig. 12 & - & 1.8 & V \\ \hline V_{CE(TH)} & Gate to Emitter Threshold Voltage & I_C = 10A, \\ \hline V_{GE} = V_{GE} & T_C = 150^\circ C & 0.75 & - & 1.8 & V \\ \hline V_{CE} = V_{GE} & SU, \\ \hline V_{CE} = Gate to Emitter Plateau Voltage & I_C = 10A, \\ \hline V_{CE} = V_{CE} & 10A, \\ \hline V_{CE} = SV, R_G = 1K\Omega & - & 0.7 & 4 & \mu s \\ \hline T_{d} & Current Turn-On Delay Time-Resistive & \\ \hline V_{CE} = 5V, R_G = 1K\Omega & - & 2.8 & 15 & \mu s \\ \hline T_{d} & Current Turn-Off Delay Time-Inductive & \\ \hline T_{d} = 25^\circ C, See Fig. 12 & - & 2.8 & 15 & \mu s \\ \hline SCIS & Self Clamped Inductive Switching & \\ \hline T_{d} = 25^\circ V, R_G = 1K\Omega & - & - & 300 & m. \\ \hline T_{d} = 25^\circ V, R_G = 1K\Omega & - & - & 300 & m. \\ \hline T_{d} = 25^\circ V, R_G = 1K\Omega & - & -$	BV <sub>ECS</sub>	Emitter t	Collector Breakdown Voltage				30	-	-	V	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	BV <sub>GES</sub>	Gate to I	Emitter Breakdown Voltage	9			±12	±14	-	V	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		Collector	to Emitter Leakage Curre	nt			-	-	25	μA	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$					See Fig. 11	Ŭ	-	-	1	mA	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	I <sub>ECS</sub>	Emitter t	o Collector Leakage Curre	ent			-	-		mA	
R2Gate to Emitter Resistance10K-26KΩState Characteristics $V_{CE(SAT)}$ Collector to Emitter Saturation Voltage $ _{C} = 6A, V_{GE} = 4V$ $T_{C} = 25^{\circ}C, V_{GE} = 125^{\circ}C, V_{GE} = 125^{\circ}C, V_{GE} = 45^{\circ}C, V_{GE} = 55^{\circ}C, See Fig. 14$ -17-nC $V_{GE(TH)}$ Gate to Emitter Threshold Voltage $I_{C} = 10A, V_{CE} = 12V, V_{CE} = 12^{\circ}C, V$					Fig. 11	T <sub>C</sub> = 150°C			40	mA	
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$ \begin{array}{c} V_{CE(SAT)} \\ V_{CE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline V_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline C_{GE(SAT)} \\ \hline C_{GE(SAT)} \\ \hline C_{GE(SAT)} \\ \hline Collector to Emitter Saturation Voltage \\ \hline C_{C} = 10A, V_{CE} = 12V, \\ \hline V_{GE} = V_{GE}, \\ \hline C_{GE(TH)} \\ \hline Cate to Emitter Plateau Voltage \\ \hline C_{C} = 10A, V_{CE} = 12V, \\ \hline T_{C} = 150^{\circ}C, \\ \hline C_{C} = 10A, V_{CE} = 12V, \\ \hline T_{C} = 100^{\circ}C, \\ \hline T_{C} = 100^{\bullet}C, \\ \hline T_{C} = 10^{\bullet}C, \\ \hline T_{C} = 10^{\bullet}C, \\ \hline T$	-	1					10K	-	26K	Ω	
$\begin{array}{ c c c c c c } \hline V_{GE} = 4V & See Fig. 3 \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 10A, & T_C = 150^\circ C, & - & 1.58 & 1.80 & V \\ \hline V_{CE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 15A, & T_C = 150^\circ C & - & 1.90 & 2.20 & V \\ \hline V_{GE(SAT)} & Collector to Emitter Saturation Voltage & I_C = 15A, & T_C = 150^\circ C & - & 1.90 & 2.20 & V \\ \hline V_{GE} = 4.5V & V_{GE} = 4.5V & T_C = 150^\circ C & - & 1.90 & 2.20 & V \\ \hline V_{GE} = 5V, See Fig. 14 & - & 17 & - & nC \\ \hline V_{GE} = 5V, See Fig. 14 & - & 17 & - & nC \\ \hline V_{GE} = 5V, See Fig. 14 & - & 17 & - & nC \\ \hline V_{GE} = 10MA, & T_C = 25^\circ C & 1.3 & - & 2.2 & V \\ \hline V_{CE} = V_{GE}, & See Fig. 10 & T_C = 150^\circ C & 0.75 & - & 1.8 & V \\ \hline V_{GE} = 0 & Gate to Emitter Threshold Voltage & I_C = 10A, V_{CE} = 12V & - & 3.0 & - & V \\ \hline V_{ICHIN} & Current Turn-On Delay Time-Resistive & V_{CE} = 14V, R_L = 1\Omega & - & 0.7 & 4 & \mu s \\ \hline t_{rR} & Current Turn-On Delay Time-Resistive & V_{CE} = 5V, R_G = 1K\Omega & - & 2.1 & 7 & \mu s \\ \hline t_{d(OFF)L} & Current Turn-Off Delay Time-Inductive & V_{CE} = 300V, L = 500\mu Hy, & - & 4.8 & 15 & \mu s \\ \hline t_{rL} & Current Fall Time-Inductive & V_{GE} = 5V, R_G = 1K\Omega & - & 2.8 & 15 & \mu s \\ \hline SCIS & Self Clamped Inductive Switching & T_J = 25^\circ C, L = 3.0 & mHy, & - & - & 300 & m. \\ \hline \end{array}$	n State (	Charact	eristics								
$\begin{array}{c} V_{GE(SAT)} & One of the analyse of the second seco$	V <sub>CE(SAT)</sub>	Collector	or to Emitter Saturation Voltage				-	1.25	1.60	V	
V <sub>GE</sub> = 4.5Vvnamic Characteristics $Q_{G(ON)}$ Gate Charge $I_C = 10A, V_{CE} = 12V, V_{GE} = 5V, See Fig. 14$ -17-nC $V_{GE(TH)}$ Gate to Emitter Threshold Voltage $I_C = 1.0mA, V_{CE} = V_{GE}, See Fig. 10$ $T_C = 25^{\circ}C$ 1.3-2.2V $V_{GE}$ $V_{GE}$ $V_{GE}$ $V_{GE}$ $T_C = 25^{\circ}C$ 1.3-2.2V $V_{GE}$ $V_{GE}$ $V_{GE}$ $V_{GE}$ $T_C = 150^{\circ}C$ $0.75$ -1.8V $V_{GEP}$ Gate to Emitter Plateau Voltage $I_C = 10A, V_{CE} = 12V$ - $3.0$ -V $V_{GEP}$ Gate to Emitter Plateau Voltage $I_C = 10A, V_{CE} = 12V$ - $3.0$ -V $V_{GEP}$ Gate to Emitter Plateau Voltage $I_C = 10A, V_{CE} = 12V$ - $3.0$ -V $V_{GEP}$ Gate to Emitter Plateau Voltage $I_C = 10A, V_{CE} = 12V$ - $3.0$ -V $V_{GEP}$ Gate to Emitter Plateau Voltage $V_{CE} = 14V, R_L = 1\Omega$ - $3.0$ -V $t_{d(ON)R}$ Current Turn-On Delay Time-Resistive $V_{CE} = 300V, L = 500\mu$ Hy,- $4.8$ $15$ $\mu$ s $t_{d(OFF)L}$ Current Turn-Off Delay Time-Inductive $V_{CE} = 300V, L = 500\mu$ Hy,- $4.8$ $15$ $\mu$ s $T_J = 25^{\circ}C, See Fig. 12$ C $2.8$ $15$ $\mu$ s $300$ $m_A$ SCISSelf Clamped Inductive Switching $T_J = 25^{\circ}C, L = 3.0$ mHy, $R_G = 1K\Omega, V_{GE} = 5V, See$ <t< td=""><td>V<sub>CE(SAT)</sub></td><td>Collector</td><td colspan="2">ector to Emitter Saturation Voltage</td><td></td><td>See Fig. 4</td><td>-</td><td>1.58</td><td>1.80</td><td></td></t<>	V <sub>CE(SAT)</sub>	Collector	ector to Emitter Saturation Voltage			See Fig. 4	-	1.58	1.80		
$      \begin{array}{c c c c c c c c c c c c c c c c c c c $	V <sub>CE(SAT)</sub>	Collector	ector to Emitter Saturation Voltage			T <sub>C</sub> = 150°C	-	1.90	2.20	V	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	vnamic (	Charact	eristics								
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Q <sub>G(ON)</sub>	Gate Ch	arge		I <sub>C</sub> = 10A, V <sub>CE</sub> = V <sub>GE</sub> = 5V, See	= 12V, Fig. 14	-	17	-	nC	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	V <sub>GE(TH)</sub>	Gate to	Emitter Threshold Voltage			-		-			
vitching Characteristics $t_{d(ON)R}$ Current Turn-On Delay Time-Resistive $V_{CE} = 14V, R_L = 1\Omega$ -0.74 $\mu$ s $t_{rR}$ Current Rise Time-Resistive $V_{GE} = 5V, R_G = 1K\Omega$ -2.17 $\mu$ s $t_{d(OFF)L}$ Current Turn-Off Delay Time-Inductive $V_{CE} = 300V, L = 500\mu$ Hy,-4.815 $\mu$ s $t_{fL}$ Current Fall Time-Inductive $V_{CE} = 5V, R_G = 1K\Omega$ -2.815 $\mu$ sSCISSelf Clamped Inductive Switching $T_J = 25^\circ$ C, L = 3.0 mHy, R_G = 1K\Omega, V_{GE} = 5V, See300m.					See Fig. 10	U	0.75	-	1.8	V	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V <sub>GEP</sub>	Gate to	Emitter Plateau Voltage		$I_{\rm C}$ = 10A, $V_{\rm CE}$	= 12V	-	3.0	-	V	
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$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	t <sub>d(ON)R</sub>	Current	Turn-On Delay Time-Resis	stive			-	0.7	4	μs	
$t_{fL}$ Current Fall Time-Inductive $V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^{\circ}C, See Fig. 12$ -2.815 $\mu s$ SCISSelf Clamped Inductive Switching $T_J = 25^{\circ}C, See Fig. 12$ 300m.R_G = 1K\Omega, V_{GE} = 5V, See Fig. 1 & 2Fig. 1 & 2300m.		Current	Rise Time-Resistive		V <sub>GE</sub> = 5V, R <sub>G</sub> = 1KΩ T <sub>J</sub> = 25°C, See Fig. 12		-	2.1	7	μs	
TLT_J = 25°C, See Fig. 12SCISSelf Clamped Inductive Switching $T_J = 25°C, L = 3.0 \text{ mHy},$ $R_G = 1K\Omega, V_{GE} = 5V, See$ Fig. 1 & 2-300m.	t <sub>d(OFF)L</sub>			tive			-	4.8	15	μs	
$R_G = 1K\Omega$ , $V_{GE} = 5V$ , See Fig. 1 & 2	t <sub>fL</sub>	Current	Fall Time-Inductive		T <sub>J</sub> = 25°C, See Fig. 12		-	2.8	15	μs	
ermal Characteristics	SCIS	Self Clar	nped Inductive Switching	$R_G = 1K\Omega$ , $V_{GE} = 5V$ , See		-	-	300	mJ		
	ermal C	haracte	eristics								

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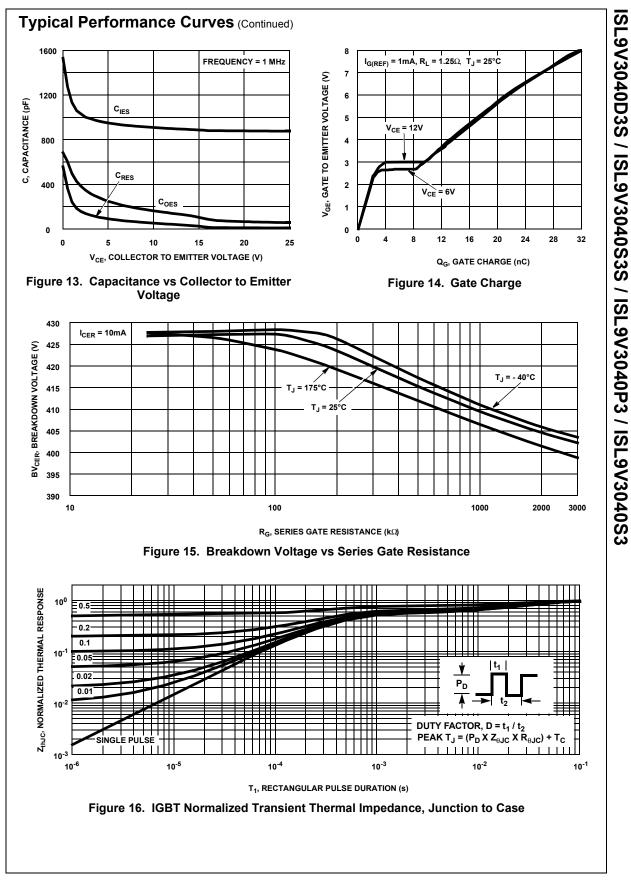


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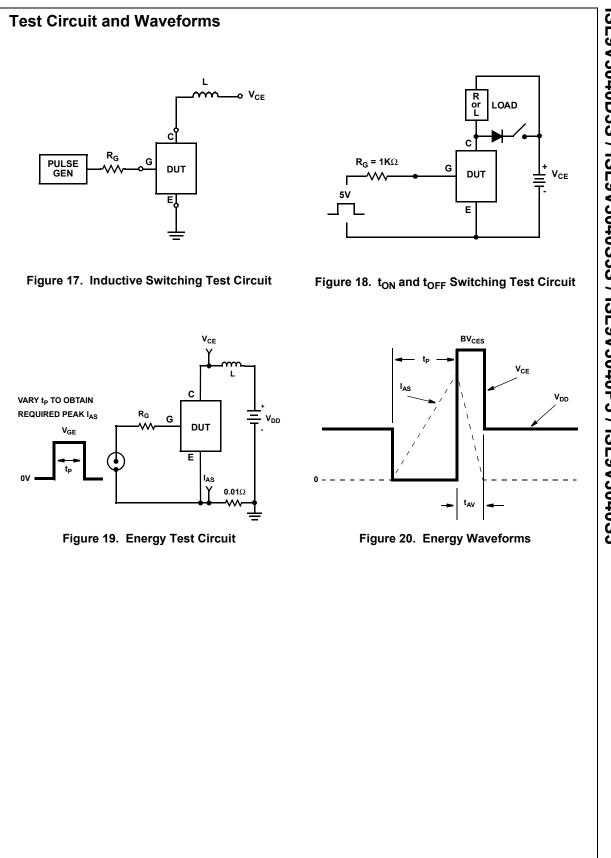
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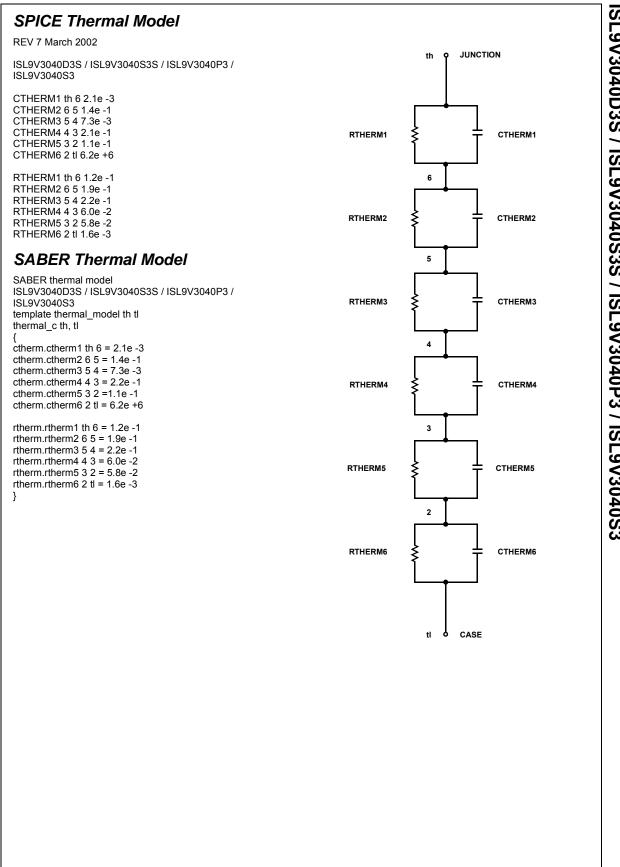


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